

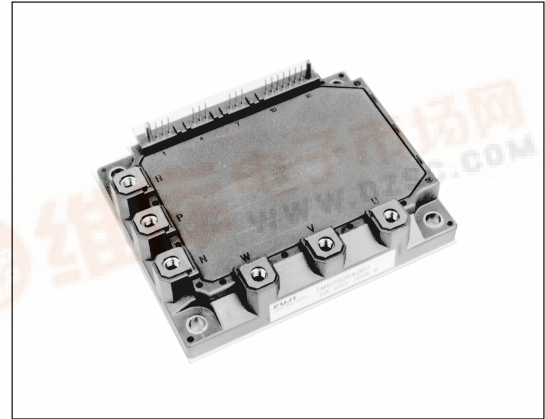
7MBP100RTB060

IPM-R3 series

600V / 100A 7 in one-package

Features

- Temperature protection provided by directly detecting the junction temperature of the IGBTs
- Low power loss and soft switching
- High performance and high reliability IGBT with overheating protection
- Higher reliability because of a big decrease in number of parts in built-in control circuit



Maximum ratings and characteristics

● Absolute maximum ratings(at Tc=25°C unless otherwise specified)

Item	Symbol	Rating		Unit		
		Min.	Max.			
Bus voltage (between terminal P and N)	DC	V _{dc}	0	450	V	
	Surge	V _{DC(surge)}	0	500	V	
	Shortoperating	V _{sc}	200	400	V	
Collector-Emitter voltage		V _{CES} *1	0	600	V	
Inverter	Collector current	DC	I _c	-	100	A
		1ms	I _{CP}	-	200	A
		Duty=72.3%	-I _c *2	-	100	A
Collector power dissipation	One transistor	P _C *3	-	347	W	
Brake	Collector current	DC	I _c	-	50	A
		1ms	I _{CP}	-	100	A
	Forward Current of Diode		I _F	-	50	A
Collector power dissipation	One transistor	P _C *3	-	198	W	
Input voltage of power supply for Pre-Driver		V _{CC} *4	-0.5	20	V	
Input signal voltage		V _{in} *5	-0.5	V _{CC} +0.5	V	
Input signal current		I _{in}	-	3	mA	
Alarm signal voltage		V _{ALM} *6	-0.5	V _{CC}	V	
Alarm signal current		I _{ALM} *7	-	20	mA	
Junction temperature		T _J	-	150	°C	
Operating case temperature		T _{CP}	-20	100	°C	
Storage temperature		T _{stg}	-40	125	°C	
Isolating voltage (Case-Terminal)		V _{iso} *8	-	AC2.5	kV	
Screw torque	Mounting (M5)		-	3.5 *9	N·m	
	Terminal (M5)		-	3.5 *9	N·m	

Note

*1 : V_{CES} shall be applied to the input voltage between terminal P and U or V or W or DB, N and U or V or W or DB.

*2 : 125°C/FWD R_{th(j-c)}/(I_c x V_F MAX)=125/0.665/(100 x 2.6)x100=72.3%

*3 : P_C=125°C/IGBT R_{th(j-c)}=125/0.36=347W [Inverter]

P_C=125°C/IGBT R_{th(j-c)}=125/0.63=198W [Break]

*4 : V_{CC} shall be applied to the input voltage between terminal No. 3 and 1, 6 and 4, 9 and 7, 11 and 10.

*5 : V_{in} shall be applied to the input voltage between terminal No. 2 and 1, 5 and 4, 8 and 7, 12,13,14,15 and 10.

*6 : V_{ALM} shall be applied to the voltage between terminal No. 16 and 10.

*7 : I_{ALM} shall be applied to the input current to terminal No. 16.

*8 : 50Hz/60Hz sine wave 1 minute.

*9 : Recommendable Value : 2.5 to 3.0 N·m

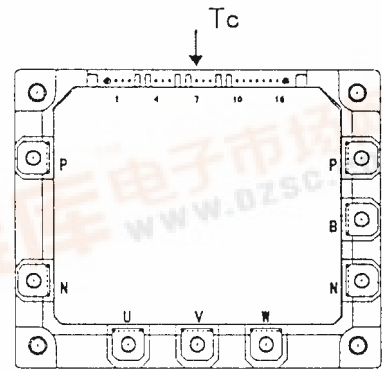


Fig.1 Measurement of case temperature

Item	Symbol	Min.	Typ.	Max.	Unit
Weight	Wt	-	450	-	g



7MBP100RTB060

IGBT-IPM

Electrical characteristics (at Tc=Tj=25°C, Vcc=15V unless otherwise specified.)

● Main circuit

Item		Symbol	Condition	Min.	Typ.	Max.	Unit	
Inverter	Collector current at off signal input	ICES	VCE=600V Vin terminal open.	-	-	1.0	mA	
	Collector-Emitter saturation voltage	VCE(sat)	Ic=100A	Terminal	-	-	2.3	V
				Chip	-	1.8	-	
	Forward voltage of FWD	VF	Ic=100A	Terminal	-	-	2.6	V
Chip				-	1.6	-		
Brake	Collector current at off signal input	ICES	VCE=600V Vin terminal open.	-	-	1.0	mA	
	Collector-Emitter saturation voltage	VCE(sat)	Ic=50A	Terminal	-	-	2.2	V
				Chip	-	1.75	-	
	Forward voltage of Diode	VF	-Ic=50A	Terminal	-	-	3.3	V
Chip				-	1.9	-	V	
Turn-on time	ton	VDC=300V, Tj=125°C		1.2	-	-	μs	
Turn-off time	toff	Ic=100A Fig.1, Fig.6		-	-	3.6		
Reverse recovery time	trr	VDC=300V, Ic=100A Fig.1, Fig.6		-	-	0.3		
Maximum Avalanche Energy (A non-repetition)	PAV	Internal wiring inductance=50nH Main circuit wiring inductance=54nH		100	-	-	mJ	

● Control circuit

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Supply current of P-line side pre-driver(one unit)	Iccp	Switching Frequency : 0 to 15kHz Tc=-20 to 125°C Fig.7	-	-	18	mA
Supply current of N-line side pre-driver	ICCN		-	-	65	mA
Input signal threshold voltage (on/off)	Vin(th)	ON	1.00	1.35	1.70	V
		OFF	1.25	1.60	1.95	V
Input zener voltage	VZ	Rin=20k ohm	-	8.0	-	V
Alarm signal hold time	tALM	Tc=-20°C Fig.2	1.1	-	-	ms
		Tc=25°C Fig.2	-	2.0	-	ms
		Tc=125°C Fig.2	-	-	4.0	ms
Limiting resistor for alarm	RALM		1425	1500	1575	ohm

● Protection Section (Vcc=15V)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Over Current Protection Level of Inverter circuit	Ioc	Tj=125°C	150	-	-	A
Over Current Protection Level of brake circuit		Tj=125°C	75	-	-	A
Over Current Protection Delay time	tDOC	Tj=125°C	-	5	-	μs
SC Protection Delay time	tsc	Tj=125°C Fig.4	-	-	8	μs
IGBT Chip Over Heating	TjOH	surface of IGBT chips	150	-	-	°C
Over Heating Protection Hysteresis	TjH		-	20	-	°C
Over Heating Protection Temperature Level	TcoH	VDC=0V, Ic=0A, Case temperature	110	-	125	°C
Over Heating Protection Hysteresis	Tch		-	20	-	
Under Voltage Protection Level	Vuv		11.0	-	12.5	V
Under Voltage Protection Hysteresis	VH		0.2	0.5	-	

● Thermal characteristics(Tc=25°C)

Item	Symbol		Min.	Typ.	Max.	Unit	
Junction to Case thermal resistance	INV	IGBT	Rth(j-c)	-	-	0.36	°C/W
		FWD	Rth(j-c)	-	-	0.665	°C/W
	Brake	IGBT	Rth(j-c)	-	-	0.63	°C/W
Case to fin thermal resistance with compound	Rth(c-f)		-	0.05	-	°C/W	

● Noise Immunity (VDC=300V, Vcc=15V, Test Circuit Fig.5)

Item	Condition	Min.	Typ.	Max.	Unit
Common mode rectangular noise	Pulse width 1μs, polarity ±, 10minuets Judge : no over-current, no miss operating	±2.0	-	-	kV
Common mode lightning surge	Rise time 1.2μs, Fall time 50μs Interval 20s, 10 times Judge : no over-current, no miss operating	±5.0	-	-	kV

● Recommendable value

Item	Symbol	Min.	Typ.	Max.	Unit
DC Bus Voltage	VDC	-	-	400	V
Operating Supply Voltage of Pre-Driver	Vcc	13.5	15.0	16.5	V

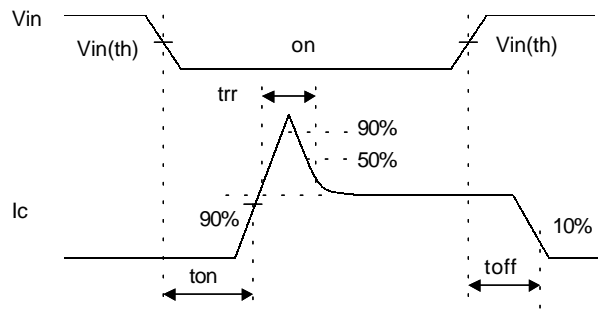
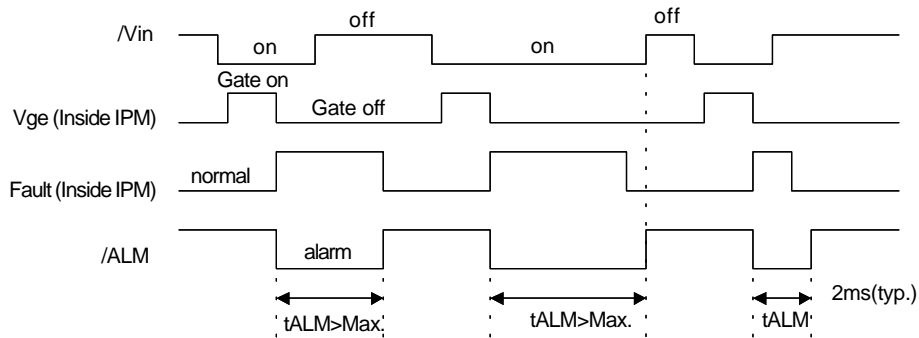


Figure 1. Switching Time Waveform Definitions



Fault : Over-current, Over-heat or Under-voltage

Figure 2. Input / Output Timing Diagram

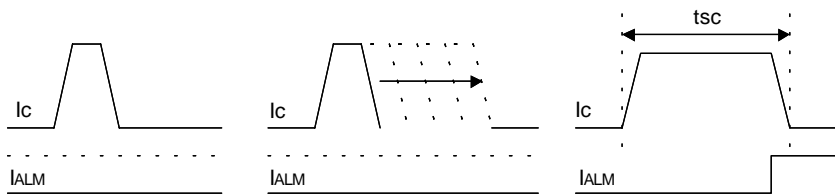


Figure 4 Definition of tsc

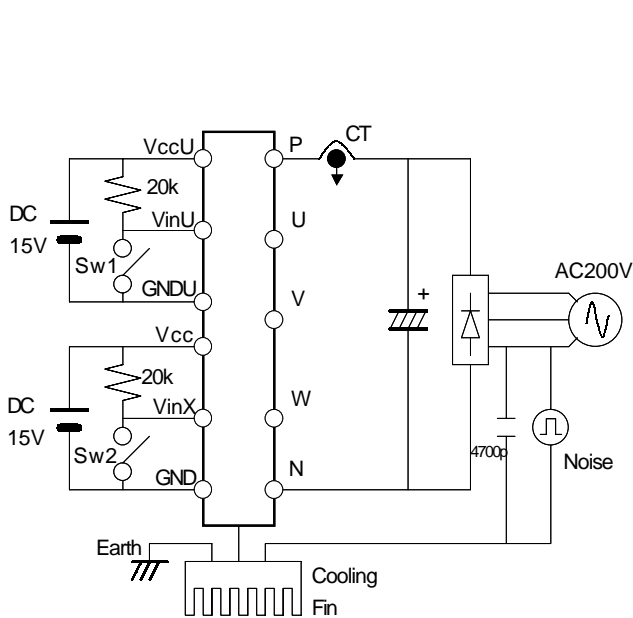


Figure 5. Noise Test Circuit

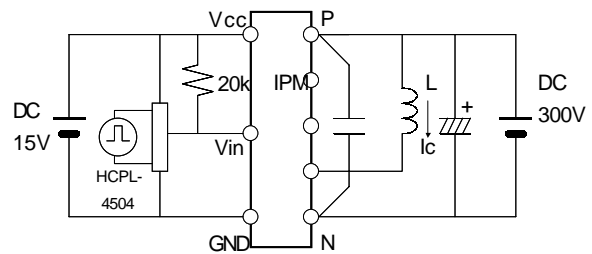


Figure 6. Switching Characteristics Test Circuit

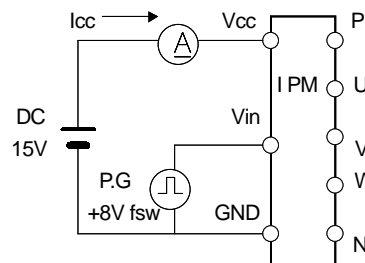
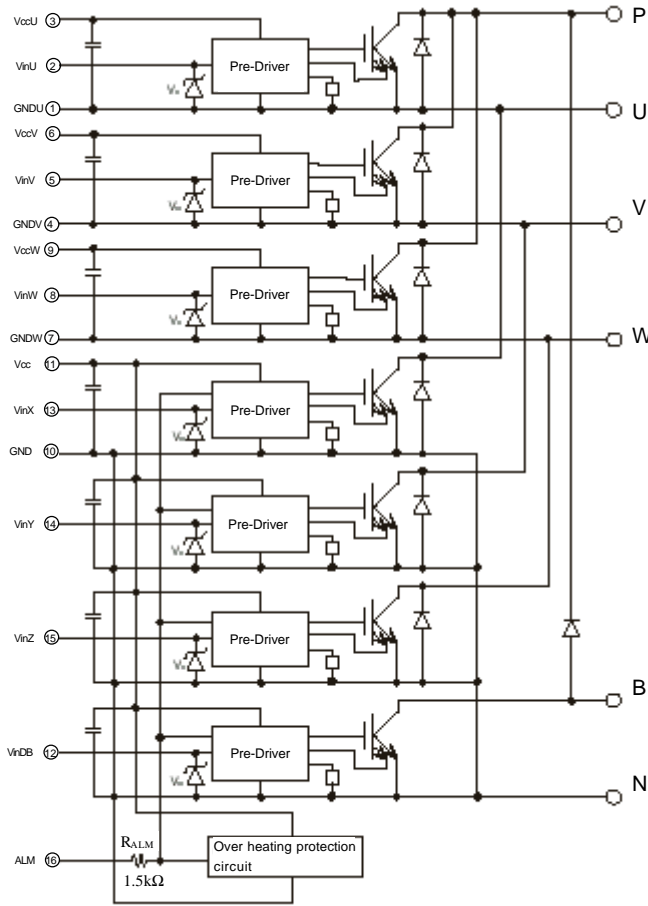


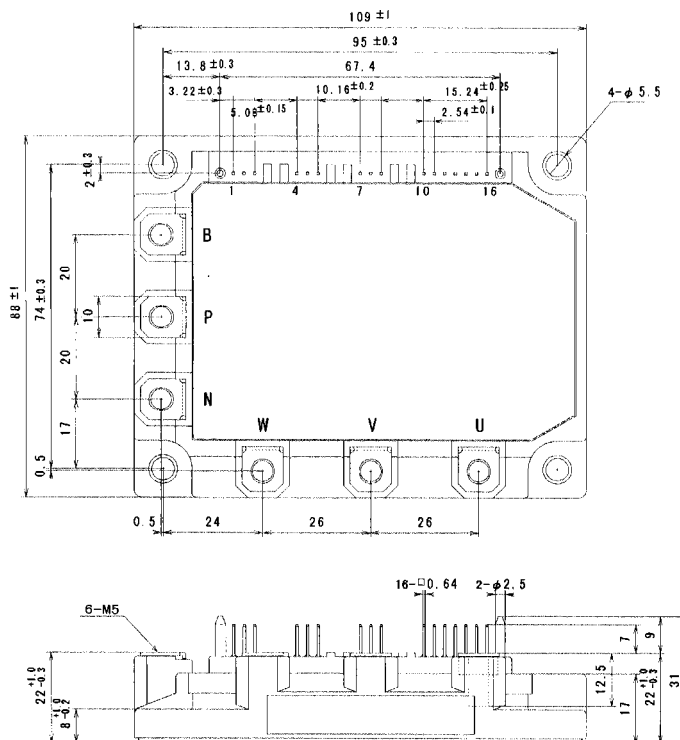
Figure 7. Icc Test Circuit

Block diagram



- Pre-driver include following functions
- ① Amplifier for drive
 - ② Short circuit protection
 - ③ Under voltage lockout circuit
 - ④ Over current protection
 - ⑤ IGBT chip over heating protection

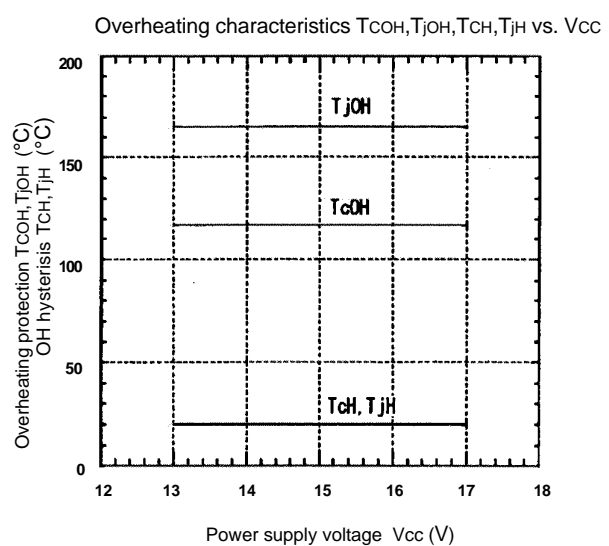
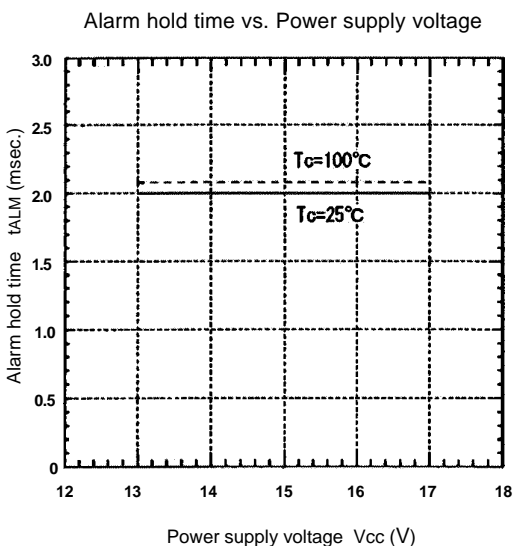
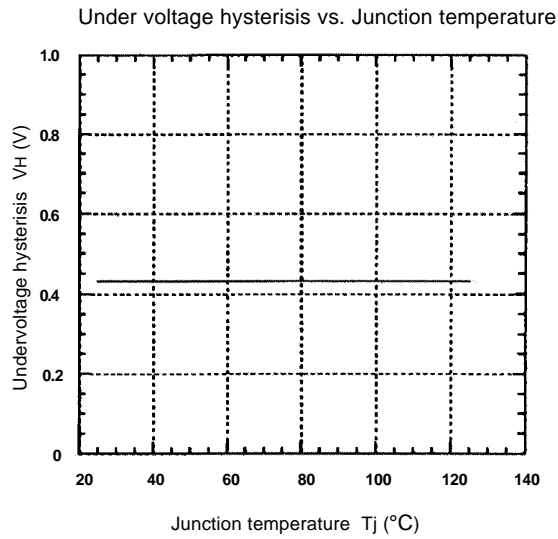
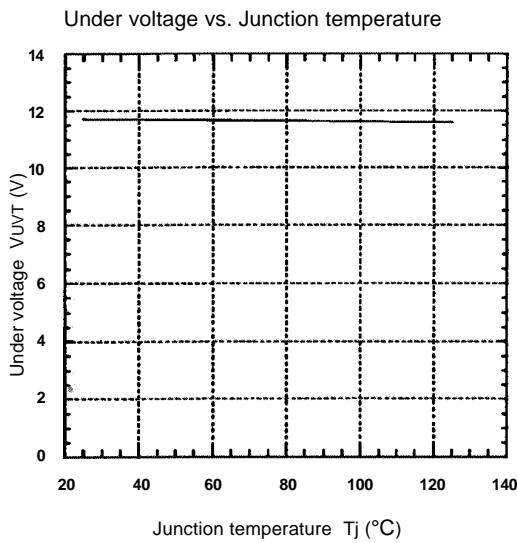
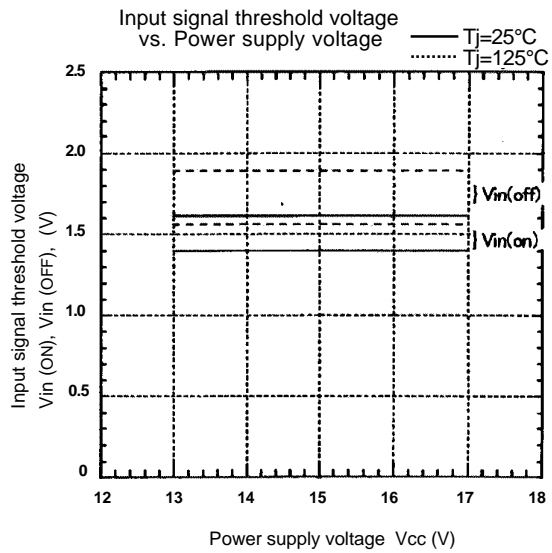
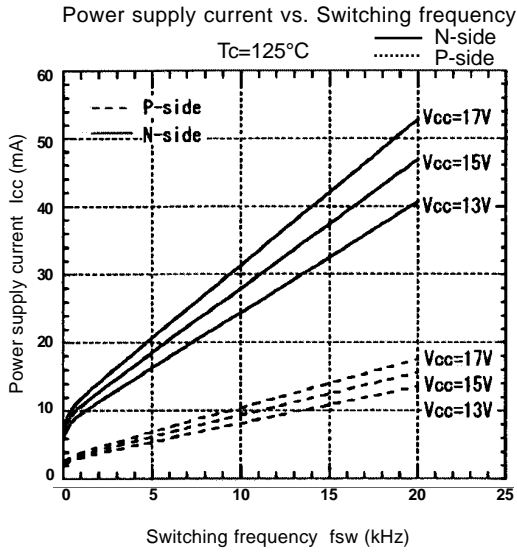
Outline drawings, mm



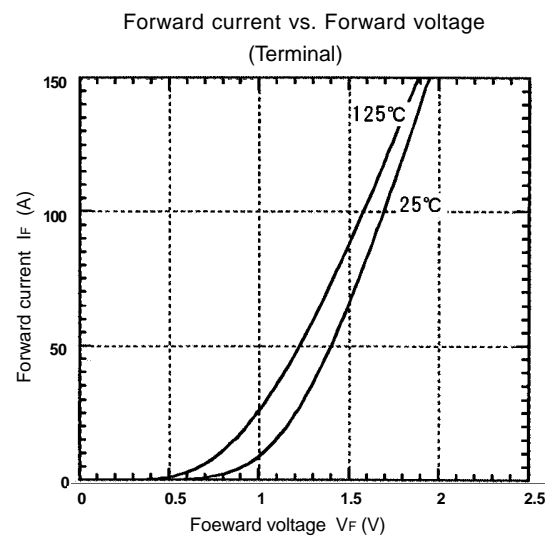
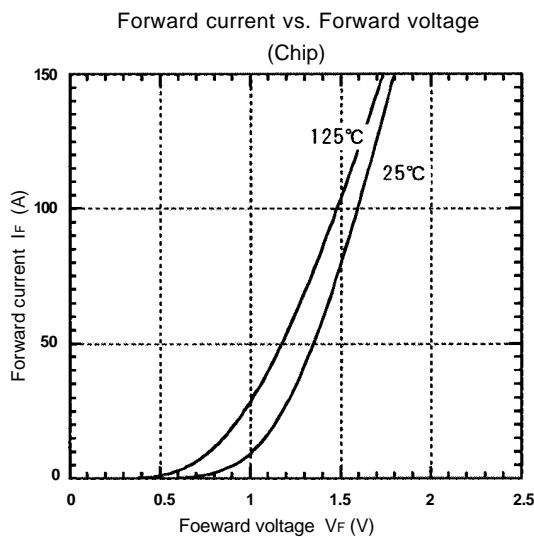
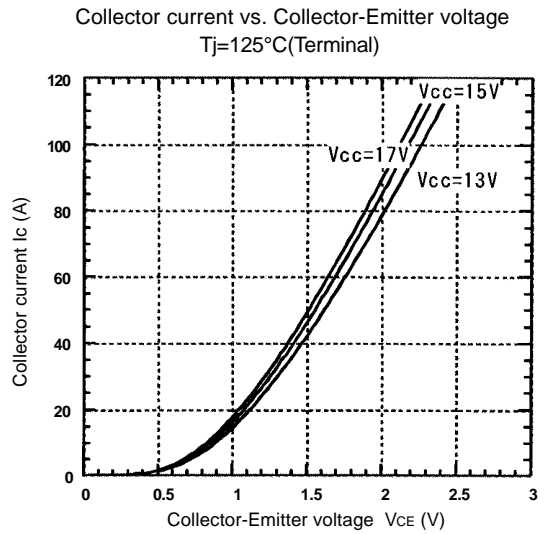
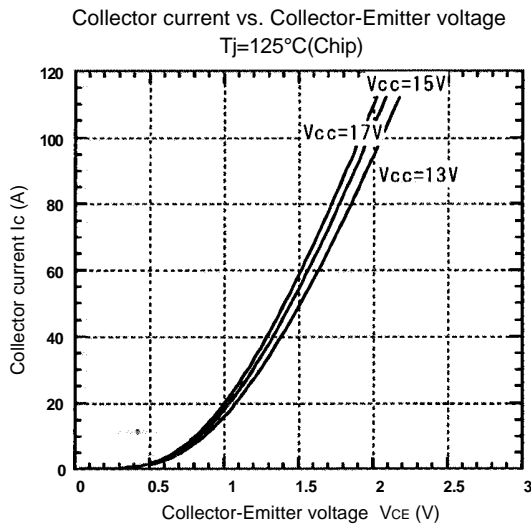
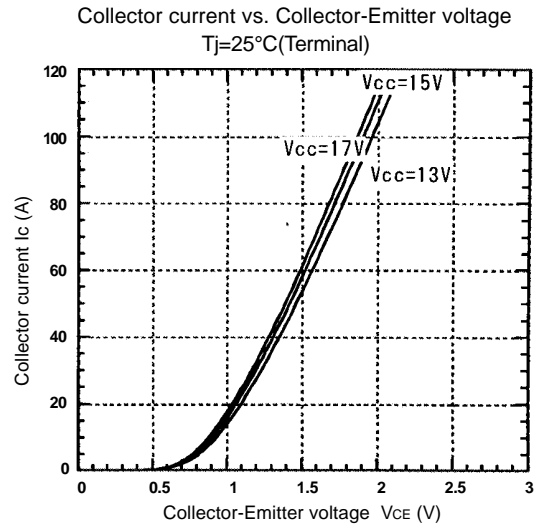
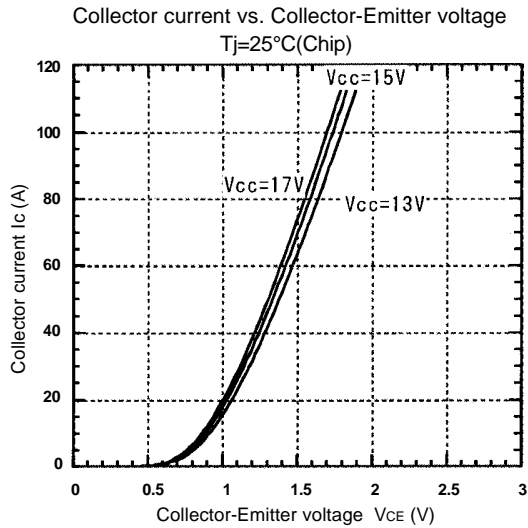
Mass : 450g

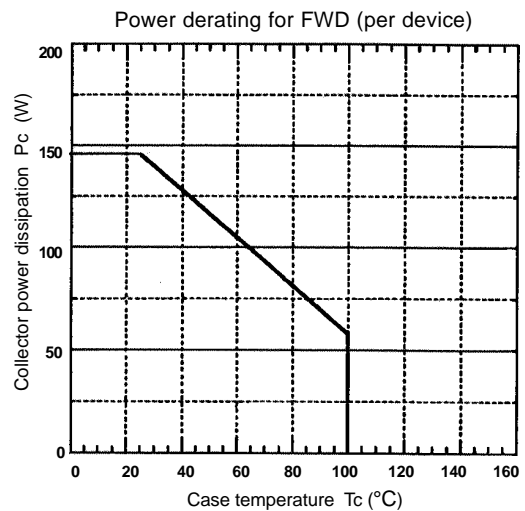
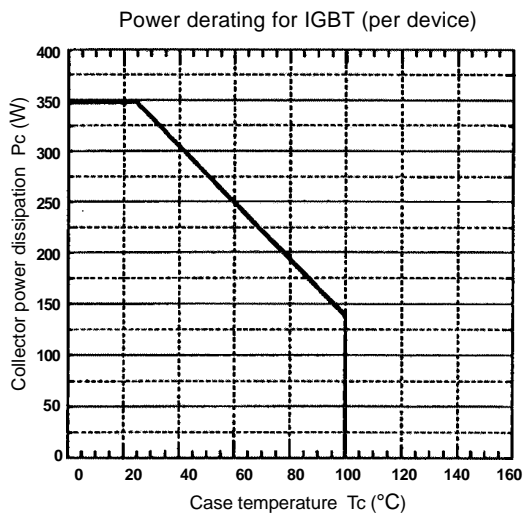
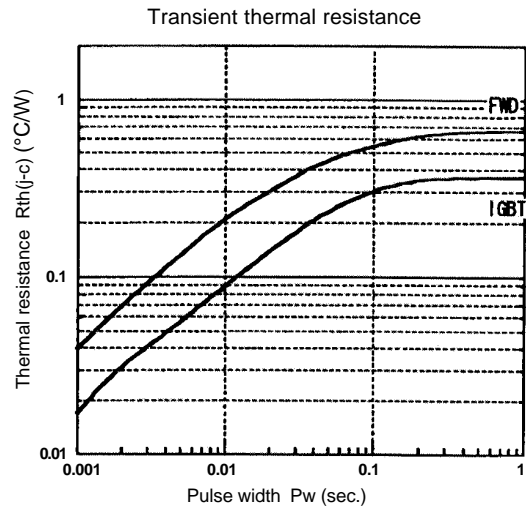
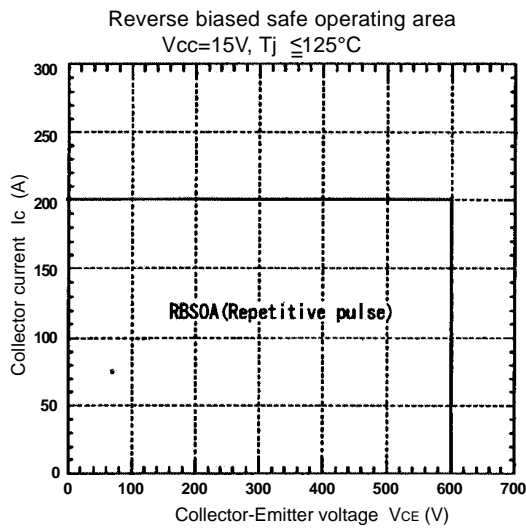
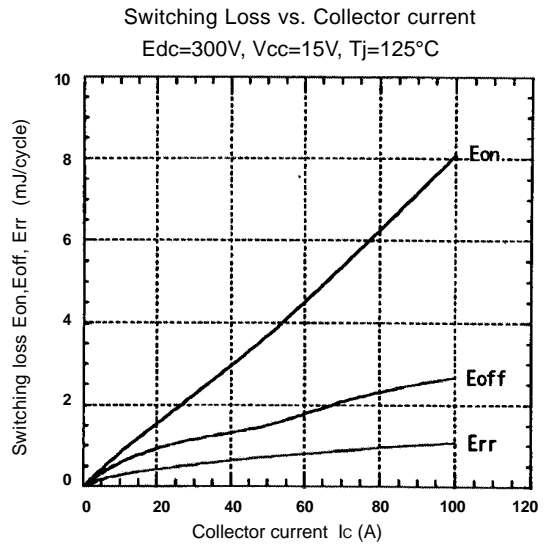
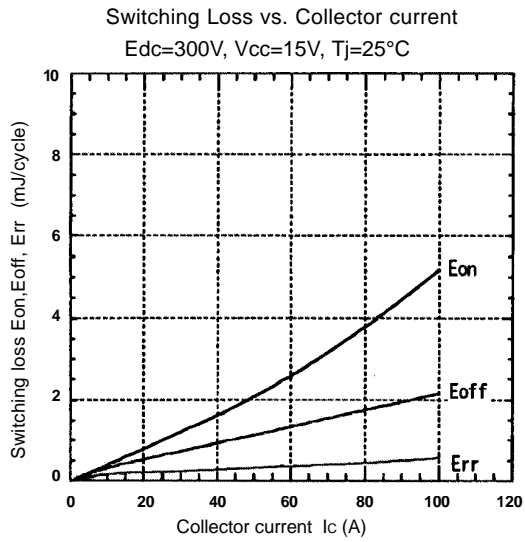
Characteristics

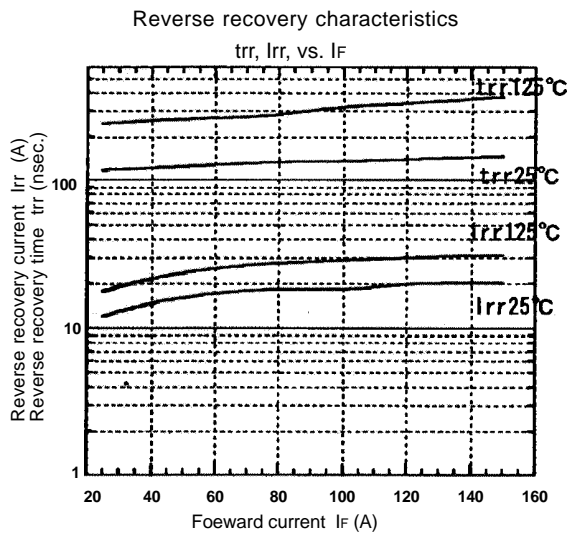
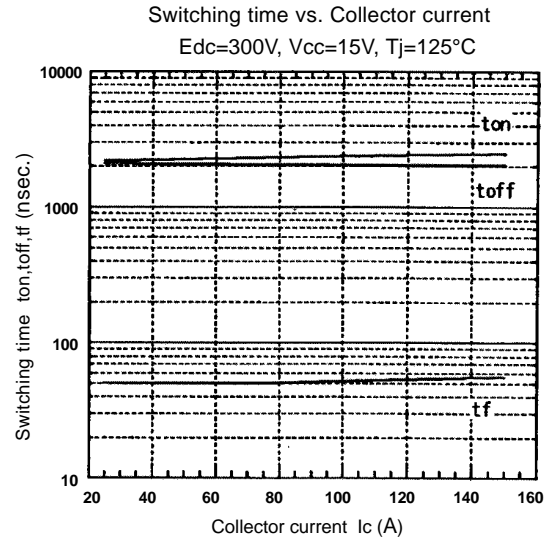
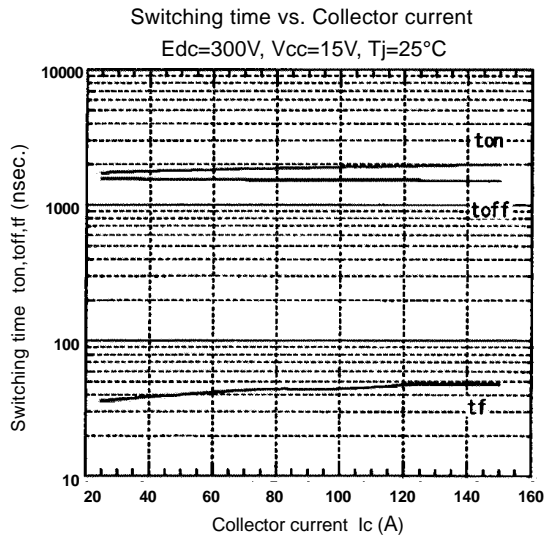
Control circuit characteristics (Representative)



● Main circuit characteristics (Representative)

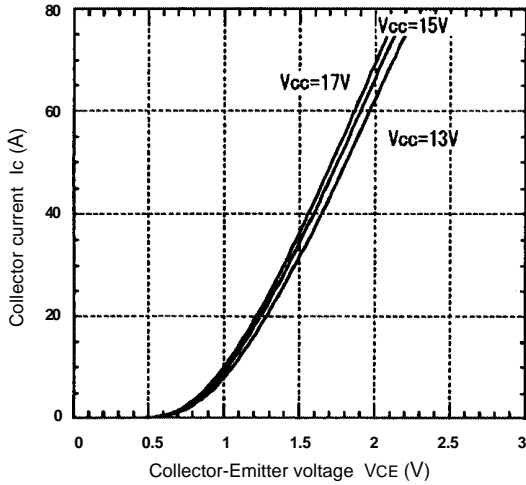




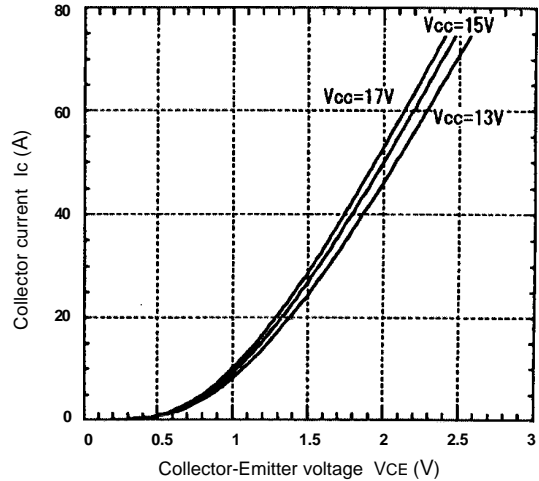


● Dynamic brake characteristics (Representative)

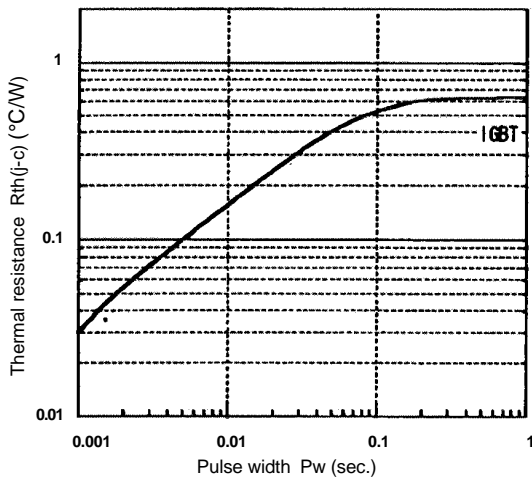
Collector current vs. Collector-Emitter voltage
T_j=25°C (Terminal)



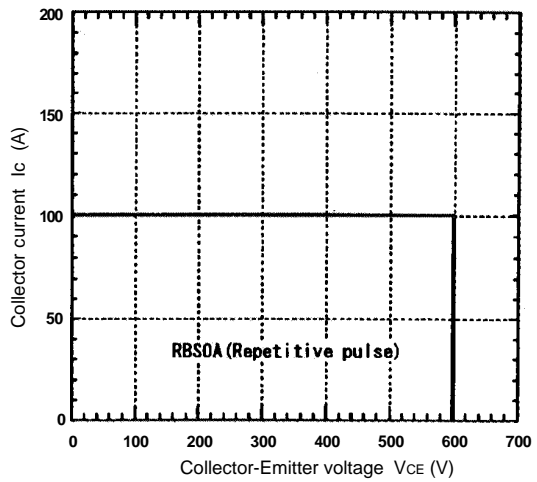
Collector current vs. Collector-Emitter voltage
T_j=125°C (Terminal)



Transient thermal resistance



Reverse biased safe operating area
V_{cc}=15V, T_j ≤ 125°C



Power derating for IGBT (per device)

